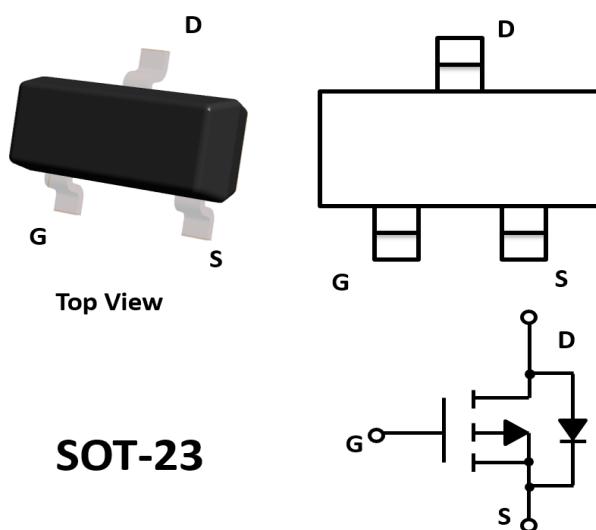


P-Channel Enhancement Mode Field Effect Transistor



Product Summary

- V_{DS} -60 V
- I_D -0.17 A
- $R_{DS(ON)}$ (at $V_{GS}=-10V$) <8 ohm
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) <10 ohm

General Description

- Trench Power LV MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge

Applications

- Video monitor
- Power management

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Unit
Drain-source Voltage	V_{DS}	-60	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current <small>$T_A=25^\circ\text{C}$ @ Steady State</small>	I_D	-0.17	A
		-0.14	
Pulsed Drain Current ^A	I_{DM}	-0.68	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$	P_D	225	mW
Thermal Resistance Junction-to-Ambient ^B	$R_{\theta JA}$	556	$^\circ\text{C} / \text{W}$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
BSS84	F2	B84.	3000	30000	120000	7" reel

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-60\text{V}, V_{\text{GS}}=0\text{V}, T_c=25^\circ\text{C}$			-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}= \pm 20\text{V}, V_{\text{DS}}=0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}= V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-0.9	-1.4	-2.0	V
Static Drain-Source On-Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}= -10\text{V}, I_{\text{D}}=-0.15\text{A}$		3.3	8	Ω
		$V_{\text{GS}}= -4.5\text{V}, I_{\text{D}}=-0.15\text{A}$		3.5	10	
Diode Forward Voltage	V_{SD}	$I_{\text{S}}=-0.17\text{A}, V_{\text{GS}}=0\text{V}$			-1.2	V
Maximum Body-Diode Continuous Current	I_{S}				-0.17	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$		30		pF
Output Capacitance	C_{oss}			10		
Reverse Transfer Capacitance	C_{rss}			5		
Switching Parameters						
Turn-on Delay Time	$t_{\text{D(on)}}$	$V_{\text{GS}}=-4.5\text{V}, V_{\text{DD}}=-30\text{V}, I_{\text{D}}=-0.15\text{A}, R_{\text{GEN}}=2.5\Omega$		2.5		ns
Turn-on Rise Time	t_r			1		
Turn-off Delay Time	$t_{\text{D(off)}}$			16		
Turn-off Fall Time	t_f			8		

A. Pulse Test: Pulse Width $\leq 300\text{us}$, Duty cycle $\leq 2\%$.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

■ Typical Performance Characteristics

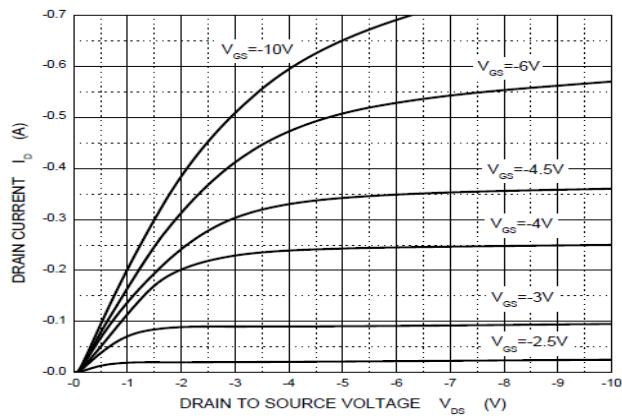


Figure1. Output Characteristics

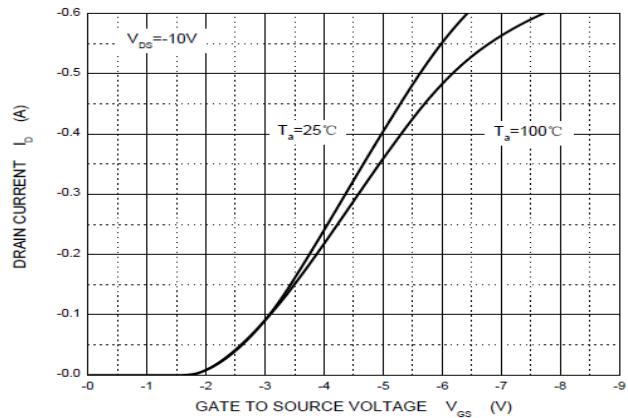


Figure2. Transfer Characteristics

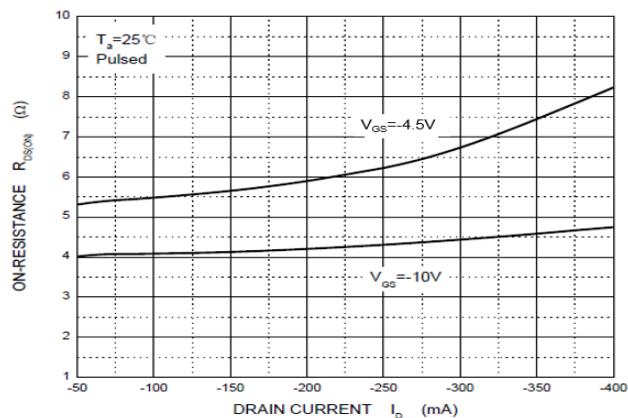


Figure3. Drain-Source on Resistance

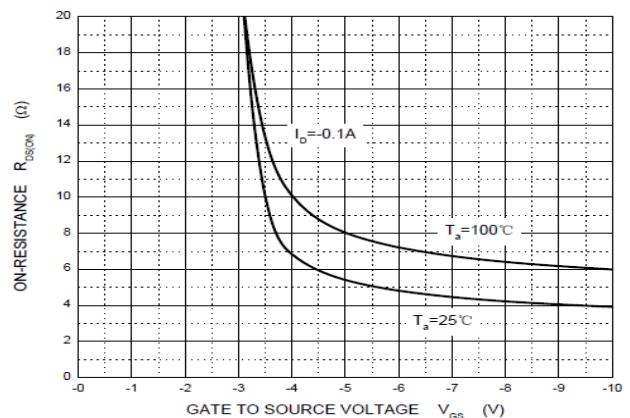


Figure4. Drain-Source on Resistance

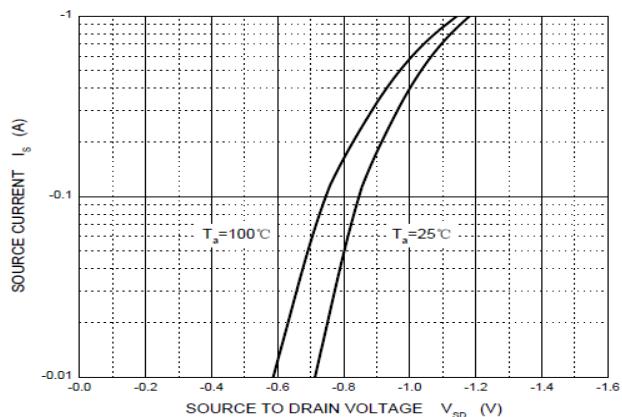


Figure5. Diode Forward Voltage vs. current

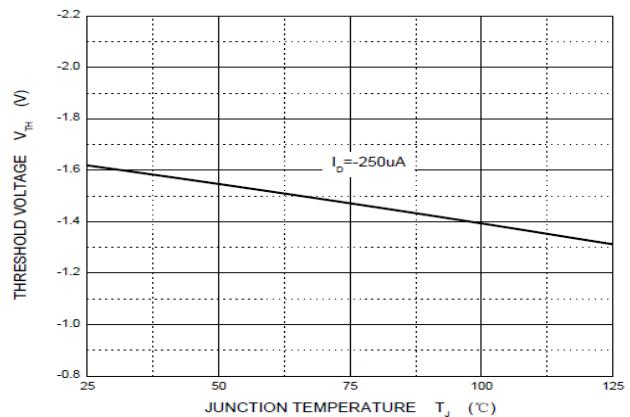
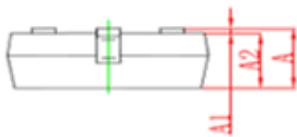
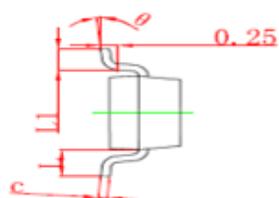
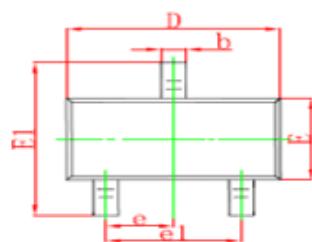
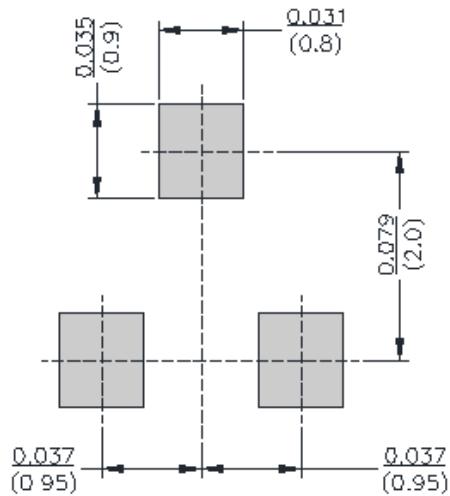


Figure6. Gate Threshold vs. Junction Temperature

■ SOT-23 Package information

Symbol	Dimensions in Millimeter		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950Type		0.037Type	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.220REF	
L1	0.300	0.500	0.012	0.020
θ	0 °	8 °	0 °	8 °

■ SOT-23 Suggested Pad Layout



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